

Title (en)
Nonvolatile semiconductor memory devices

Title (de)
Nichtflüchtige Halbleiterspeichervorrichtungen

Title (fr)
Dispositifs de mémoire à semi-conducteurs non volatile

Publication
EP 1830364 A1 20070905 (EN)

Application
EP 07109268 A 20020130

Priority
• EP 02250636 A 20020130
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Abstract (en)
A nonvolatile semiconductor memory device including a plurality of digit lines (GBL) to which a plurality of nonvolatile memory cells (MC) are connected, wherein the digit lines include a first digit line (GBL) to which a selected one of the nonvolatile memory cells (MC) is connected; and a second digit line (GBL) to which only non-selected nonvolatile memory cells (MC) are connected, the nonvolatile semiconductor memory device further comprising a selecting portion (SS) provided for every predetermined number of the digit lines (GBL) and for, upon reading memory cell information, selecting both the first and second digit lines (GBL) and, upon writing memory cell information, selecting only the first digit line (GBL).

IPC 8 full level
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Citation (search report)
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